STARPOWER

SEMICONDUCTOR **IGBT**

GD800HFA120C6SD

1200V/800A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as hybrid and electric vehicle.

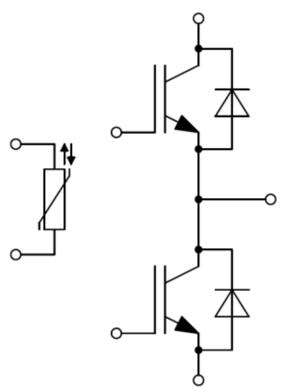
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Hybrid and electric vehicle
- Inverter for motor drive
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=100°C	800	A
I_{CM}	Pulsed Collector Current t_p=1ms	1600	A
P_D	Maximum Power Dissipation @ T_{vj}=175°C	4687	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	900	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	1800	A
I_{FSM}	Surge Forward Current t_p=10ms @ T_{vj}=125°C @ T_{vj}=175°C	2392 2448	A
I^2t	I^2t-value,t_p=10ms @ T_{vj}=125°C @ T_{vj}=175°C	28608 29964	A^2s

Module

Symbol	Description	Value	Unit
T_{vjmax}	Maximum Junction Temperature	175	°C
T_{vjop}	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	4000	V

IGBT Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=800A,V_{GE}=15V, T_{vj}=25°C		1.40	1.85	V
		I_C=800A,V_{GE}=15V, T_{vj}=125°C		1.60		
		I_C=800A,V_{GE}=15V, T_{vj}=175°C		1.60		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=24.0mA,V_{CE}=V_{GE}, T_{vj}=25°C	5.5	6.3	7.0	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_{vj}=25°C			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_{vj}=25°C			400	nA
R_{Gint}	Internal Gate Resistance			0.5		Ω
C_{ies}	Input Capacitance	V_{CE}=25V,f=100kHz, V_{GE}=0V		85.2		nF
C_{res}	Reverse Transfer Capacitance			0.45		nF
Q_G	Gate Charge	V_{GE}=-15…+15V		6.15		μC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=800A, R_G=0.5Ω, L_S=40nH, V_{GE}=-8V/+15V, T_{vj}=25°C		168		ns
t_r	Rise Time			78		ns
$t_{d(off)}$	Turn-Off Delay Time			428		ns
t_f	Fall Time			123		ns
E_{on}	Turn-On Switching Loss			43.4		mJ
E_{off}	Turn-Off Switching Loss			77.0		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=800A, R_G=0.5Ω, L_S=40nH, V_{GE}=-8V/+15V, T_{vj}=125°C		172		ns
t_r	Rise Time			84		ns
$t_{d(off)}$	Turn-Off Delay Time			502		ns
t_f	Fall Time			206		ns
E_{on}	Turn-On Switching Loss			86.3		mJ
E_{off}	Turn-Off Switching Loss			99.1		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=800A, R_G=0.5Ω, L_S=40nH, V_{GE}=-8V/+15V, T_{vj}=175°C		174		ns
t_r	Rise Time			90		ns
$t_{d(off)}$	Turn-Off Delay Time			531		ns
t_f	Fall Time			257		ns
E_{on}	Turn-On Switching Loss			99.8		mJ
E_{off}	Turn-Off Switching Loss			105		mJ
I_{SC}	SC Data	t_P≤8μs,V_{GE}=15V, T_{vj}=150°C,V_{CC}=800V, V_{CEM}≤1200V		2600		A
		t_P≤6μs,V_{GE}=15V, T_{vj}=175°C,V_{CC}=800V, V_{CEM}≤1200V		2500		A

Diode Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=900A,V_{GE}=0V,T_{vj}=25°C		1.60	2.00	V
		I_F=900A,V_{GE}=0V,T_{vj}=125°C		1.60		
		I_F=900A,V_{GE}=0V,T_{vj}=175°C		1.50		
Q_r	Recovered Charge	V_R=600V,I_F=800A, -di/dt=7778A/μs,V_{GE}=-8V, L_S=40nH,T_{vj}=25°C		47.7		μC
I_{RM}	Peak Reverse Recovery Current			400		A
E_{rec}	Reverse Recovery Energy			13.6		mJ
Q_r	Recovered Charge	V_R=600V,I_F=800A, -di/dt=7017A/μs,V_{GE}=-8V, L_S=40nH,T_{vj}=125°C		82.7		μC
I_{RM}	Peak Reverse Recovery Current			401		A
E_{rec}	Reverse Recovery Energy			26.5		mJ
Q_r	Recovered Charge	V_R=600V,I_F=800A, -di/dt=6380A/μs,V_{GE}=-8V, L_S=40nH,T_{vj}=175°C		110		μC
I_{RM}	Peak Reverse Recovery Current			413		A
E_{rec}	Reverse Recovery Energy			34.8		mJ

NTC Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		kΩ
ΔR/R	Deviation of R_{100}	T_C=100 °C,R_{100}=493.3Ω	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}exp[B_{25/80}(1/T_2-1/(298.15K))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}exp[B_{25/100}(1/T_2-1/(298.15K))]$		3433		K

Module Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.80		mΩ
R_{thJC}	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)			0.032 0.049	K/W
R_{thCH}	Case-to-Heatsink (per IGBT) Case-to-Heatsink (per Diode) Case-to-Heatsink (per Module)		0.030 0.046 0.009		K/W
M	Terminal Connection Torque, Screw M6 Mounting Torque, Screw M5	3.0 3.0		6.0 6.0	N.m
G	Weight of Module		350		g

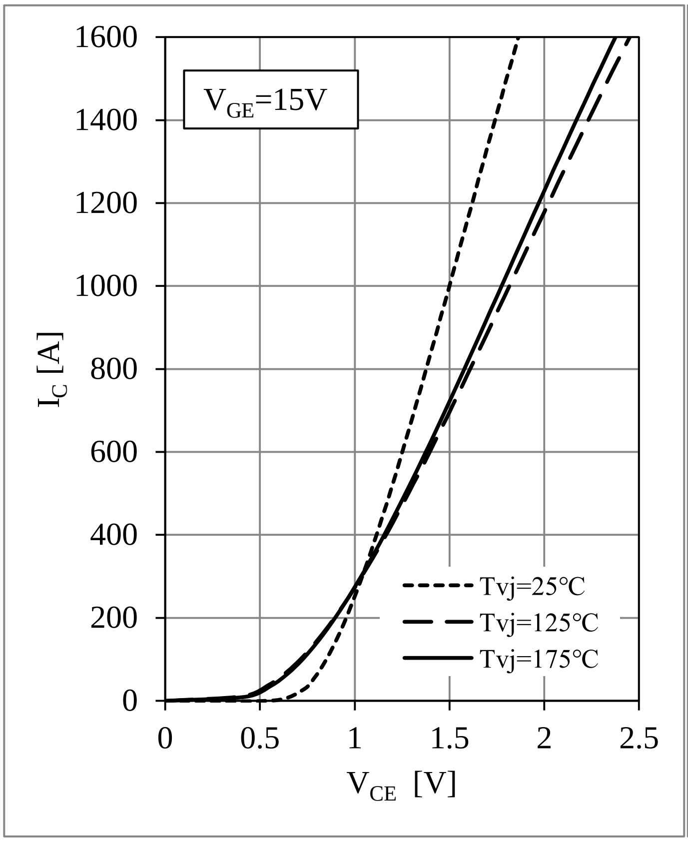


Fig 1. IGBT Output Characteristics

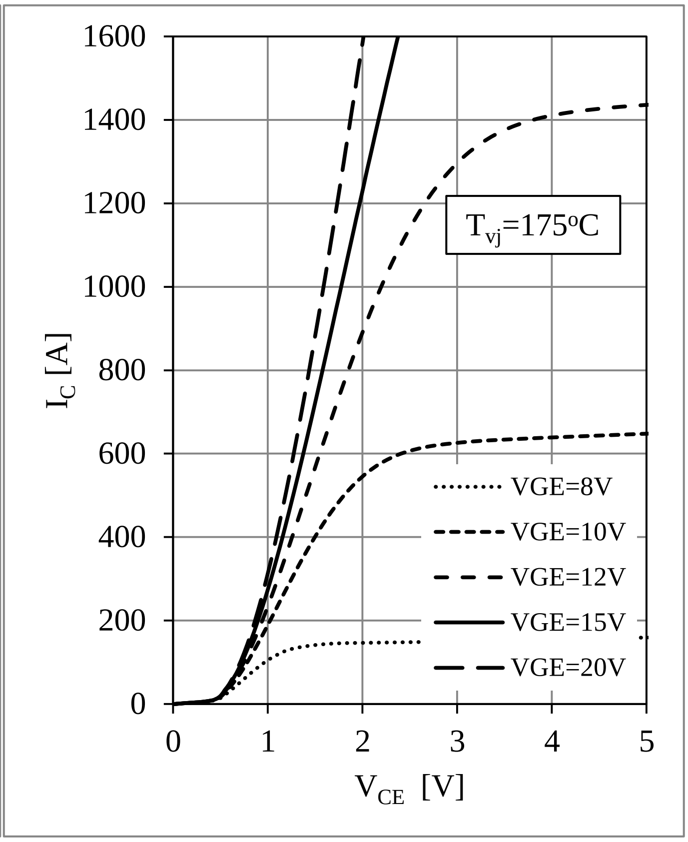


Fig 2. IGBT Transfer Characteristics

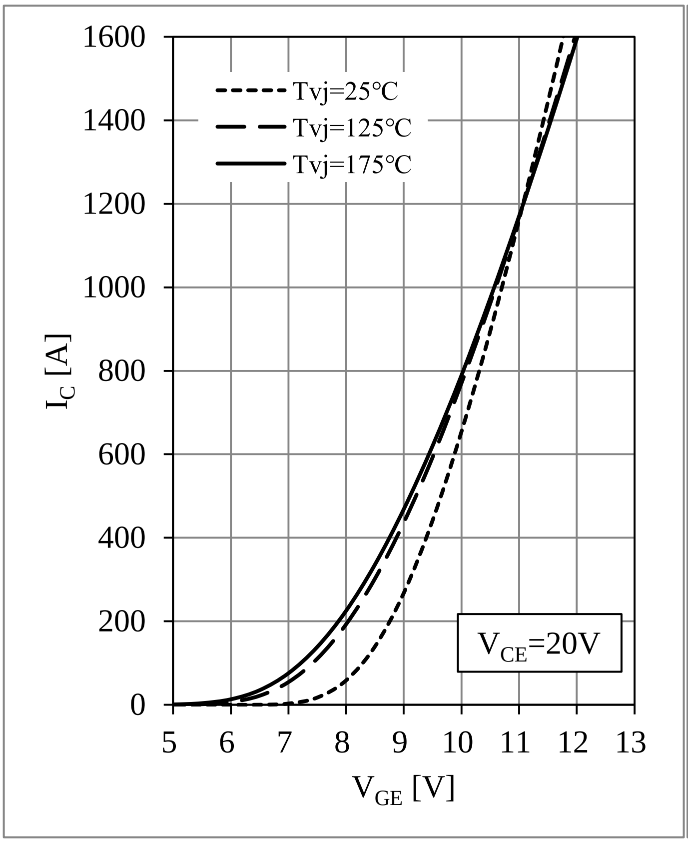


Fig 3. IGBT Transfer Characteristics

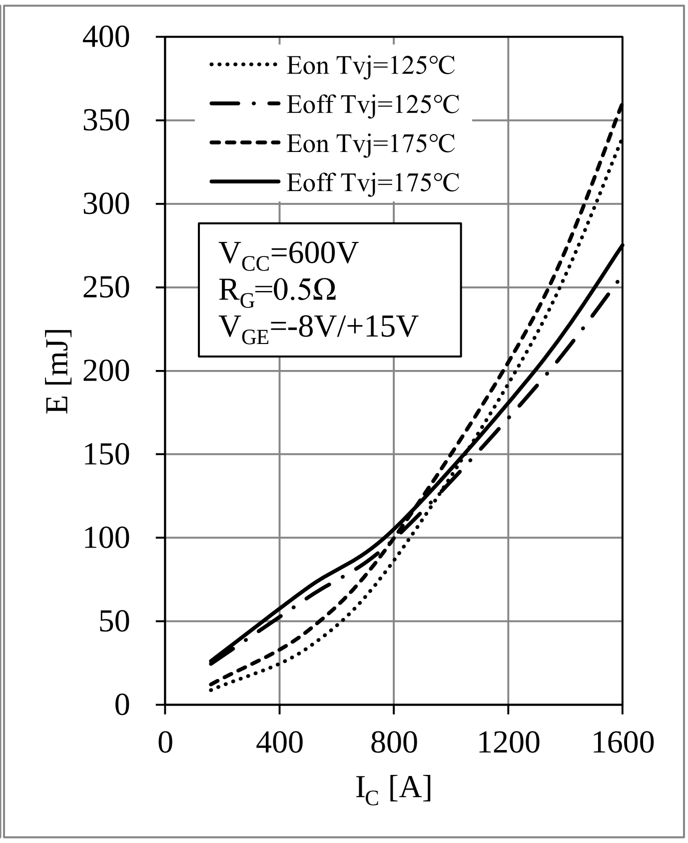


Fig 4. IGBT Switching Loss vs. I_C

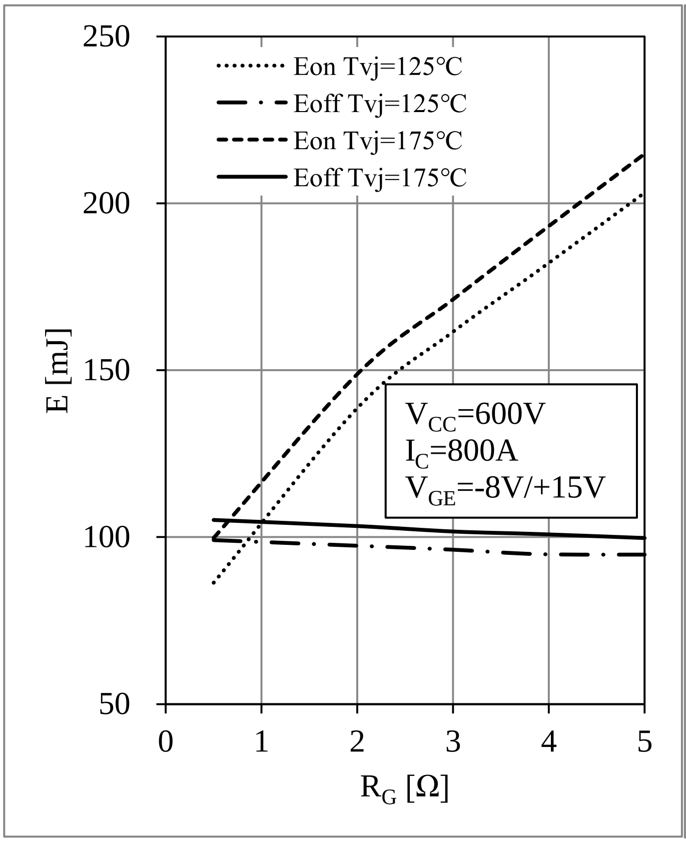


Fig 5. IGBT Switching Loss vs. R_G

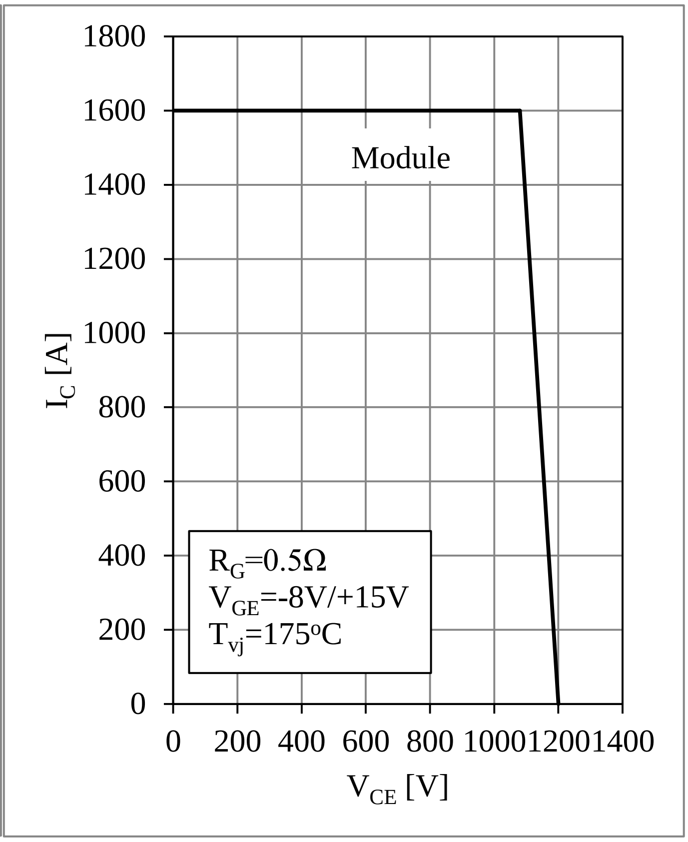


Fig 6. RBSOA

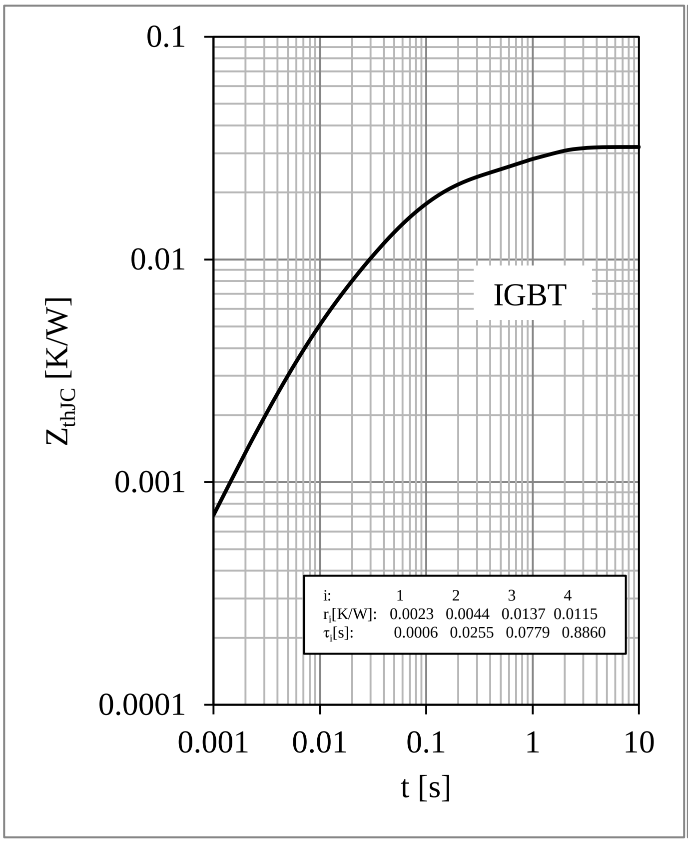


Fig 7. IGBT Transient Thermal Impedance

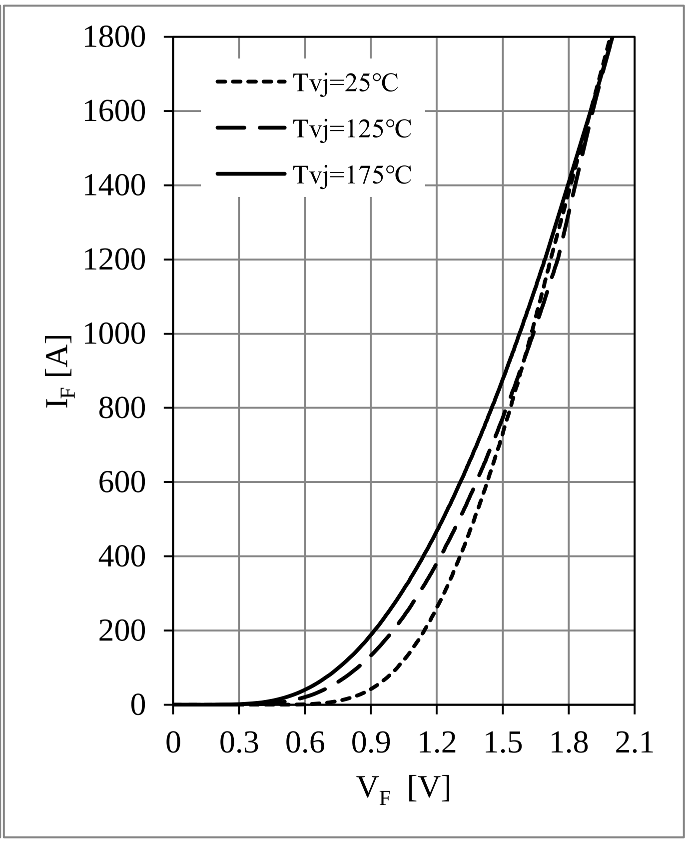


Fig 8. Diode Forward Characteristics

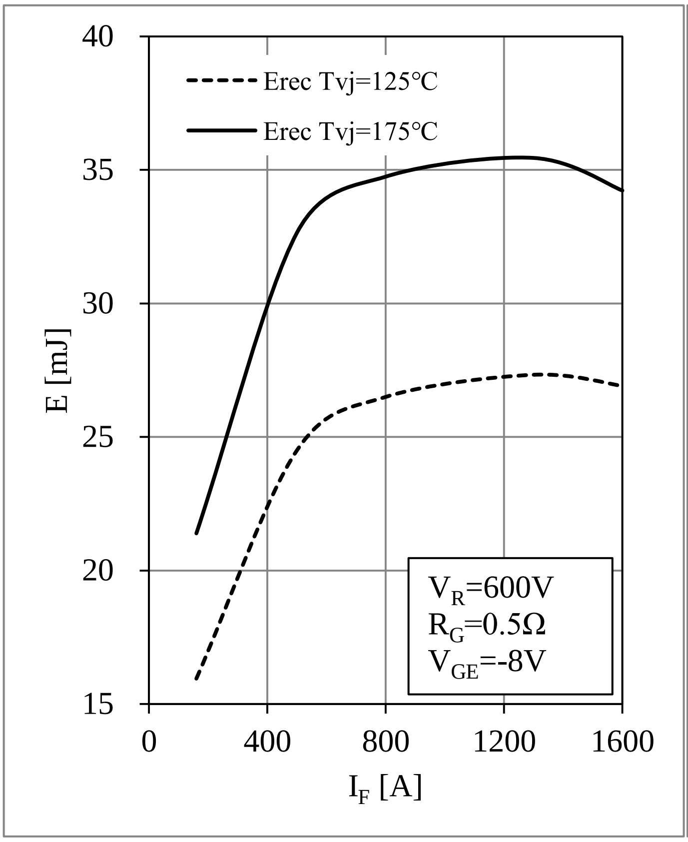


Fig 9. Diode Switching Loss vs. I_F

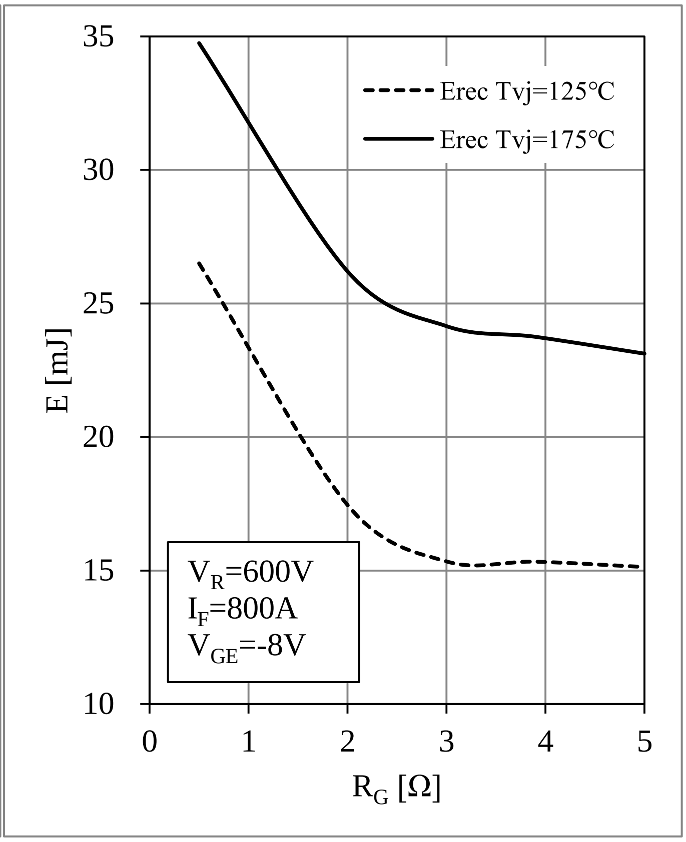


Fig 10. Diode Switching Loss vs. R_G

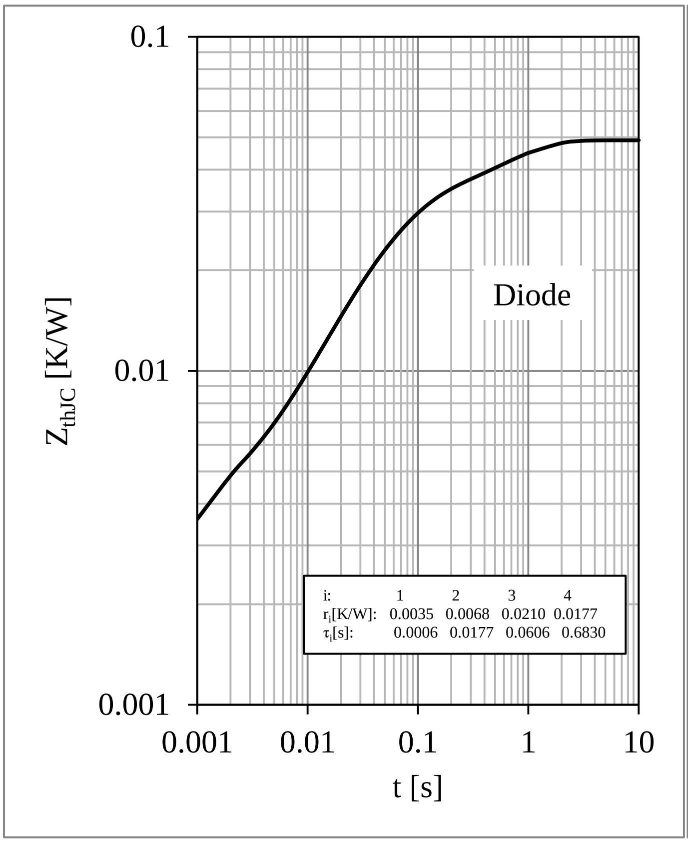


Fig 11. Diode Transient Thermal Impedance

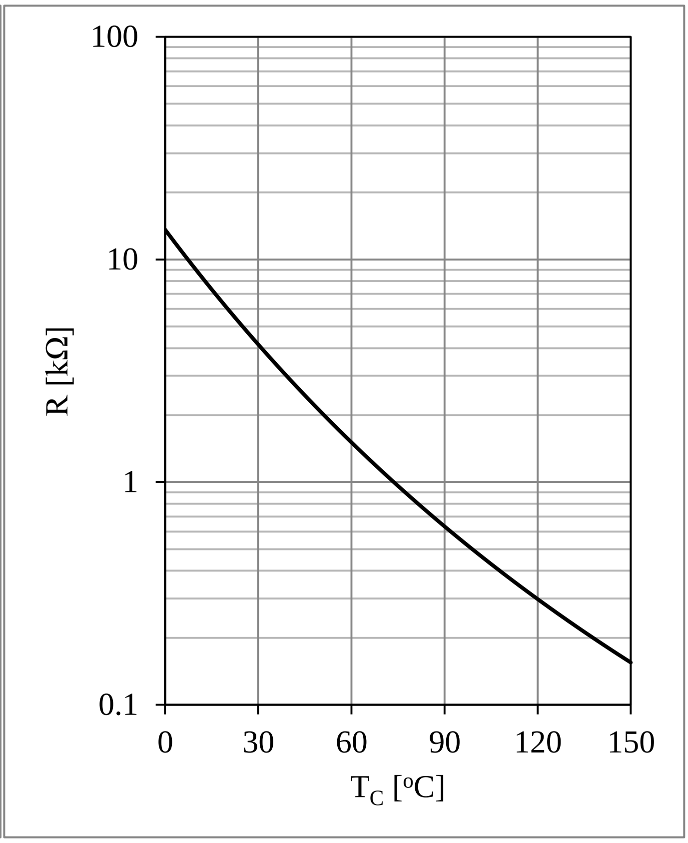
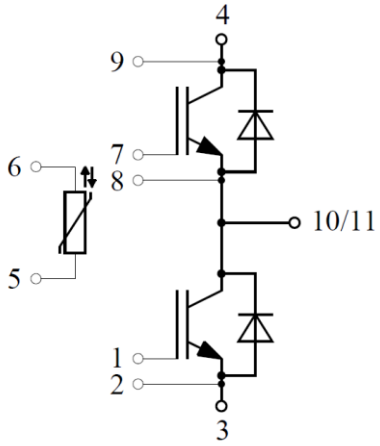


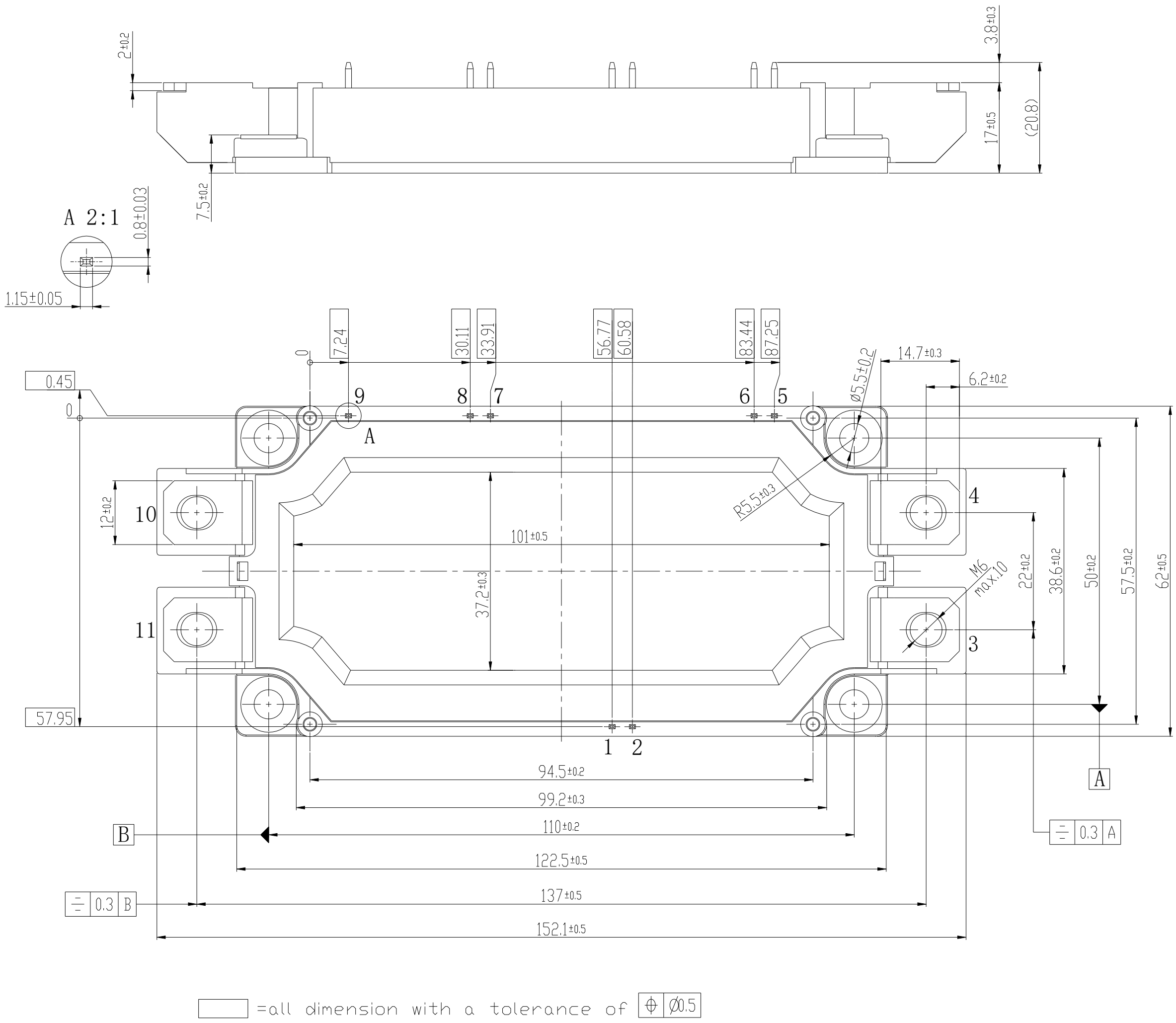
Fig12. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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